

ABSTRACT OF THE DISCLOSURE

The invention discloses a crosslinked chemical-amplification positive-working photoresist composition of good pattern resolution and storage stability, which is suitable for pattern size diminution by the thermal flow process after development. The composition comprises: (A) a polyhydroxystyrene resin substituted for a part of the hydroxyl hydrogen atoms by acid-dissociable solubility-reducing groups; (B) a radiation-sensitive acid-generating compound; (C) a polyvinyl ether compound as a crosslinking agent; (D) a carboxylic acid; and (E) an amine compound.

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